

A	2020.12.20	All	AOS-AONS36302		

/ Descriptions

PDFN5×6 N
N-Channel MOSFET in a PDFN5×6 Plastic Package .

/ Features

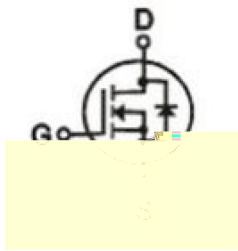
Low $R_{DS(ON)}$ to minimize conductive loss, low Gate Charge for fast switching, Low Thermal resistance, HF Product.

/ Applications

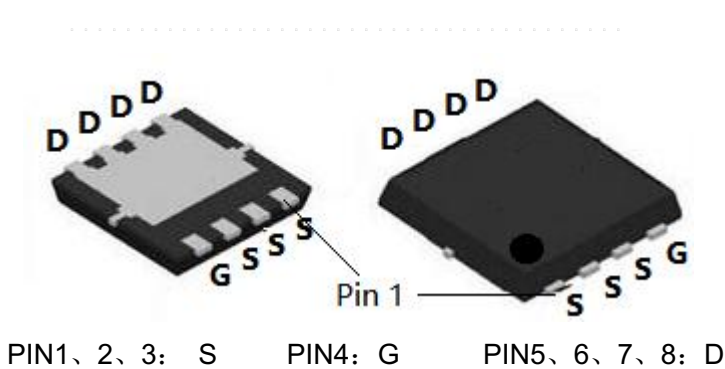
MB/NB/UMPC/VGA Buck -

Battery Management, High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA, Networking DC-DC Power System, Load Switch.

/ Equivalent Circuit



/ Pinning



Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

/ h_{FE} Classifications & Marking

“ ” 。 See Marking Instructions.



/ Absolute Maximum Ratings(T_a=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Drain Current - Continuous	I _D	146	A
Drain Current – Pulsed	I _{DM}	300	A
Gate-Source Voltage	V _{GS}	±20	V
Power Dissipation	P _D (T _c =25°C)	57	W
Single Pulse Avalanche Energy(L=0.5mH)	E _{AS}	315	mJ
Avalanche Current(L=0.5mH)	I _{AS}	30	A
Junction and Storage Temperature Range	T _j , T _{stg}	-55 to 150	°C
Thermal resistance, junction - ambient	t ≤ 10s	R _{θJA}	°C/W
	Steady-State		
Thermal resistance, junction - case	Steady-State	R _{θJC}	2.2

/ Electrical Characteristics(T_a=25)

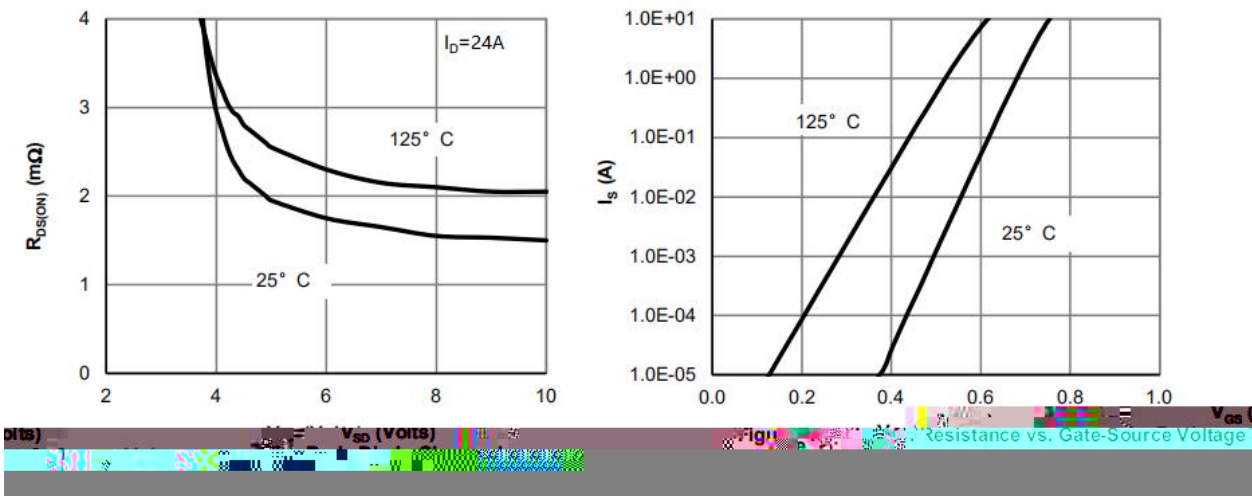
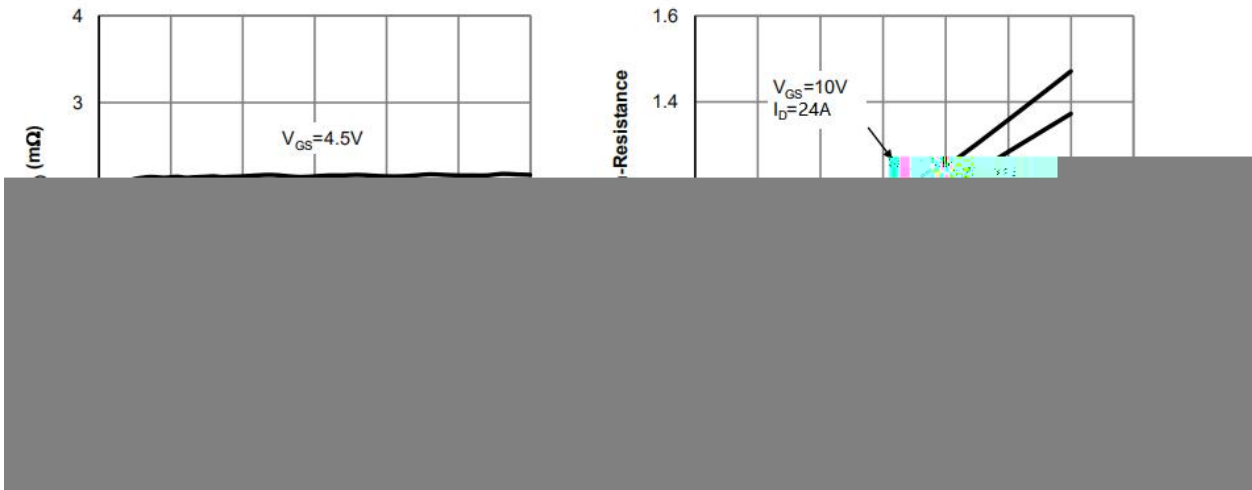
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250uA, V _{GS} =0V	30	35		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1.0	uA
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} = ±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.6	3	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =24A		1.5	1.8	mΩ
		V _{GS} =4.5V, I _D =12A		2.0	2.8	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V		0.68	1	V
Input Capacitance	C _{iSS}	V _{DS} =25V, V _{GS} =0V f=1.0MHz		8500		pF
Output Capacitance	C _{oss}			890		
Reverse Transfer Capacitance	C _{rSS}			670		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V f=1MHz		1.8		Ω
Total Gate Charge	Q _{g(10V)}	V _{GS} =10V, V _{DS} =15V, I _D =20A		60		nC
Total Gate Charge	Q _{g(4.5V)}			28		
Gate Source Charge	Q _{gs}			12		
Gate Drain Charge	Q _{gd}			9.5		



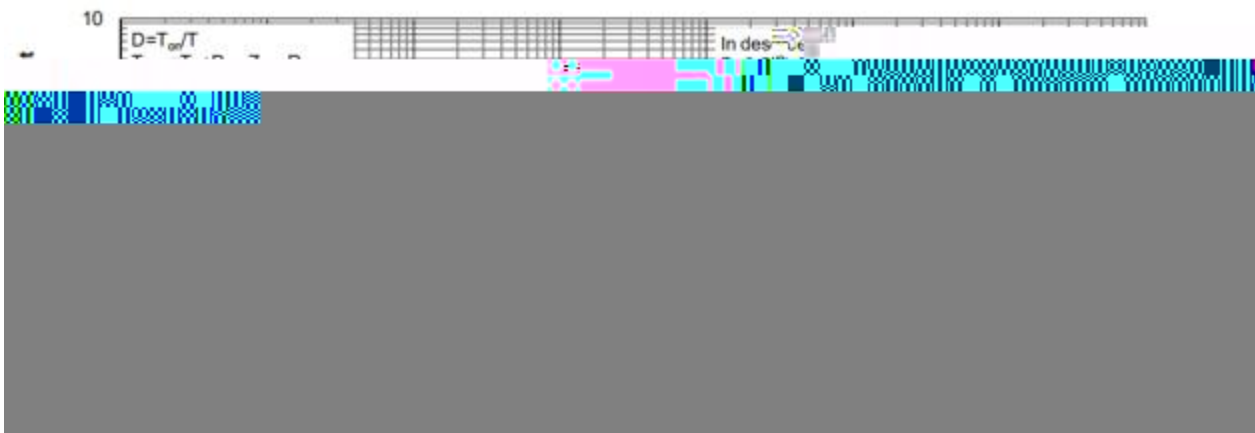
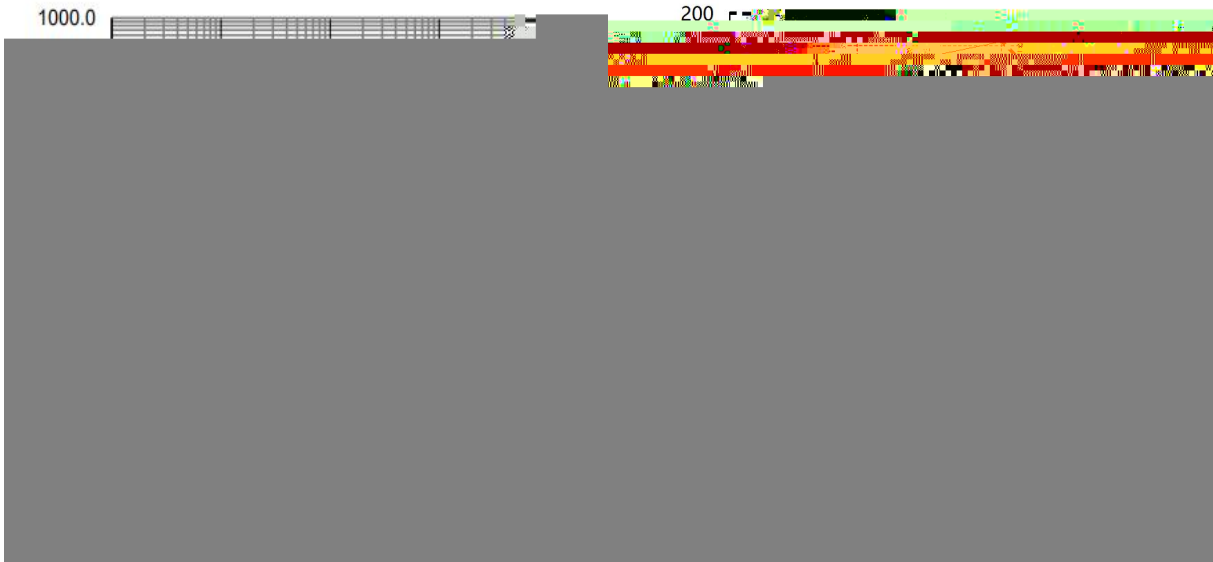
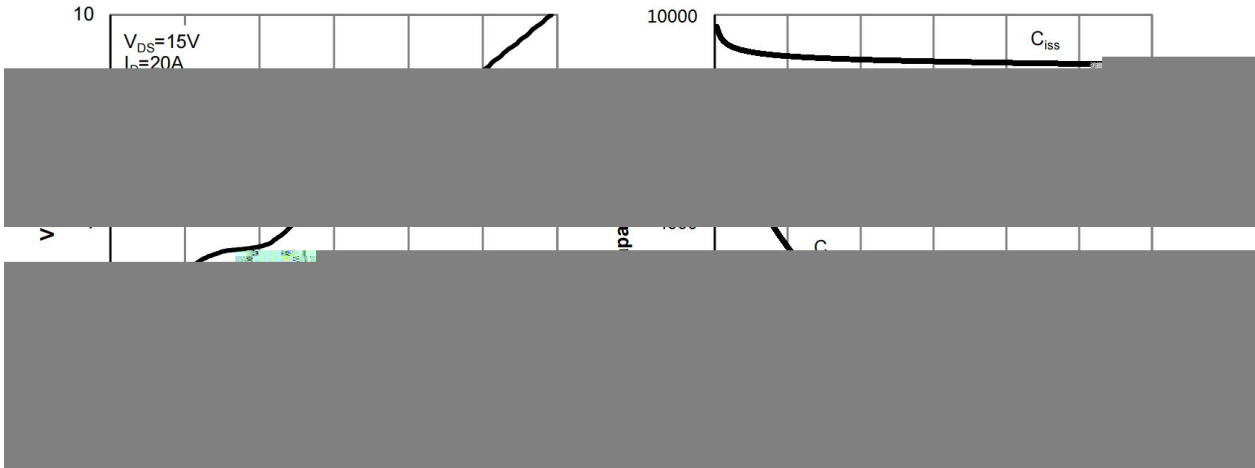
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		12.5		ns
Turn-On Rise Time	t_r			6.0		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	t_f			10.5		

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

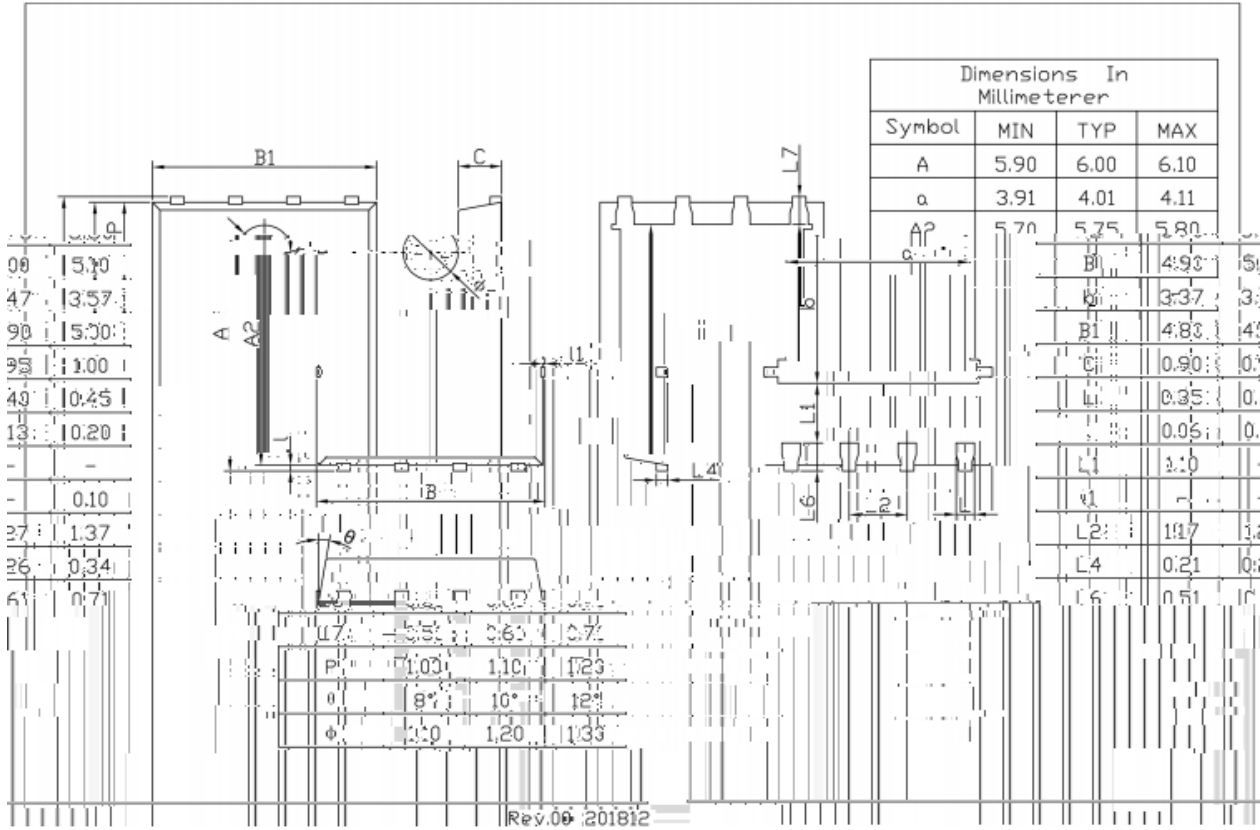




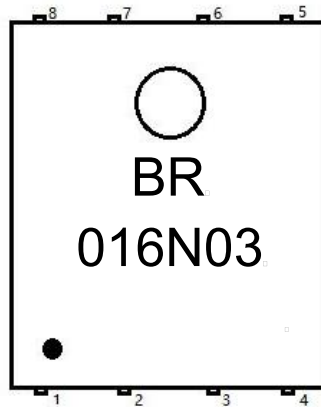
/ Package Dimensions

PDFN5 X6

Unit:mm



/ Marking Instructions



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016N03' (%/ + ,

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Note:

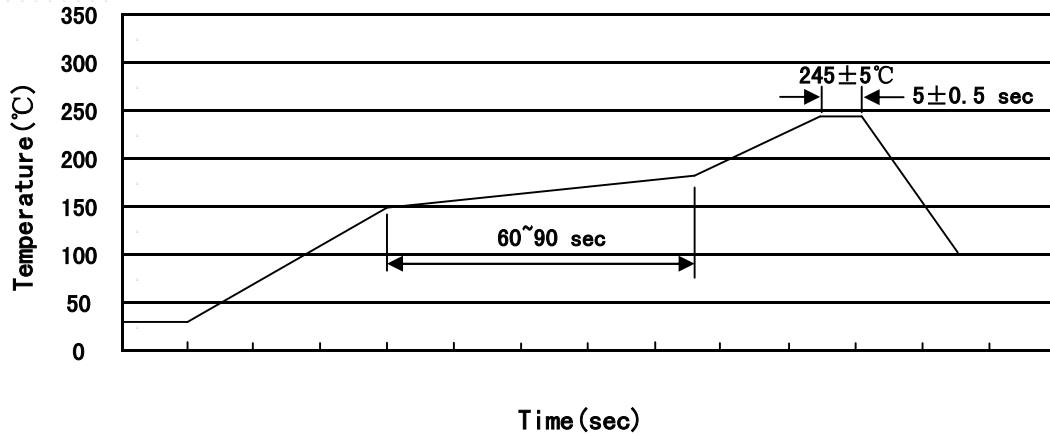
BR: Company Code.

016N03: Product Type Code.

****: Lot No. Code, code change with Lot No.



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1 150 180 60 90sec; 1.Preheating:150~180°C, Time:60~90sec.
- 2 245±5 5±0.5sec; 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
- 3 2 10°C/sec. 3. Cooling Speed: 2~10°C/sec.

/ Resistance to Soldering Heat Test Conditions

260±5°C 10±1 sec. Temp.:260±5°C Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只/卷盘	卷盘/盒	只/盒	盒/箱	只/箱	盒		箱
PDFN5 × 6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

/ Notices